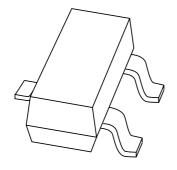
DISCRETE SEMICONDUCTORS

DATA SHEET



PMBD6050 High-speed diode

Product data sheet Supersedes data of 1999 May 11 2004 Jan 14



High-speed diode

PMBD6050

FEATURES

• Small plastic SMD package

• High switching speed: max. 4 ns

• Continuous reverse voltage: max. 70 V

• Repetitive peak reverse voltage: max. 85 V

• Repetitive peak forward current: max. 500 mA.

APPLICATIONS

• High-speed switching in thick and thin-film circuits.

DESCRIPTION

The PMBD6050 is a high-speed switching diode fabricated in planar technology, and encapsulated in a small SOT23 plastic SMD package.

MARKING

| TYPE NUMBER | MARKING CODE(1) |
|-------------|-----------------|
| PMBD6050 | *5A |

Note

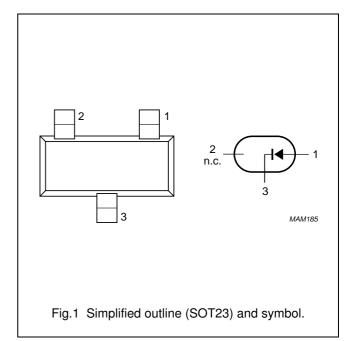
1. * = p: Made in Hong Kong.

* = t : Made in Malaysia.

* = W : Made in China.

PINNING

| PIN | DESCRIPTION | |
|-----|---------------|--|
| 1 | anode | |
| 2 | not connected | |
| 3 | cathode | |



ORDERING INFORMATION

| TYPE | PACKAGE | | | | | |
|----------|---------|--|-------|--|--|--|
| NUMBER | NAME | NAME DESCRIPTION VERSION | | | | |
| PMBD6050 | _ | plastic surface mounted package; 3 leads | SOT23 | | | |

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|-------------------------------------|--|------|------|------|
| V _{RRM} | repetitive peak reverse voltage | | _ | 85 | V |
| V_R | continuous reverse voltage | | _ | 70 | ٧ |
| l _F | continuous forward current | note 1; see Fig.2 | _ | 215 | mA |
| I _{FRM} | repetitive peak forward current | | _ | 500 | mA |
| I _{FSM} | non-repetitive peak forward current | square wave; $T_j = 25$ °C prior to surge; see Fig.4 | | | |
| | | t = 1 μs | _ | 4 | Α |
| | | t = 1 ms | _ | 1 | Α |
| | | t = 1 s | _ | 0.5 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C; note 1 | _ | 250 | mW |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| Tj | junction temperature | | _ | 150 | °C |

Note

1. Device mounted on an FR4 printed-circuit board.

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ELECTRICAL CHARACTERISTICS

 T_j = 25 °C unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MAX. | UNIT |
|-----------------|--------------------------|---|------|------|
| V _F | forward voltage | see Fig.3 | | |
| | | I _F = 1 mA | 715 | mV |
| | | I _F = 10 mA | 855 | mV |
| | | I _F = 50 mA | 1 | V |
| | | I _F = 150 mA | 1.25 | V |
| I_R | reverse current | see Fig.5 | | |
| | | V _R = 50 V | 100 | nA |
| | | V _R = 50 V; T _j = 150 °C | 50 | μΑ |
| C _d | diode capacitance | $f = 1 \text{ MHz}$; $V_R = 0$; see Fig.6 | 1.5 | pF |
| t _{rr} | reverse recovery time | when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA; see Fig.7 | 4 | ns |
| V _{fr} | forward recovery voltage | when switched from $I_F = 10$ mA; $t_r = 20$ ns; see Fig.8 | 1.75 | V |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|-----------------------|---|------------|-------|------|
| R _{th(j-tp)} | thermal resistance from junction to tie-point | | 330 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | note 1 | 500 | K/W |

Note

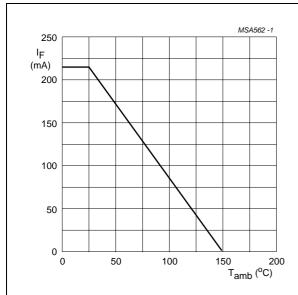
1. Device mounted on an FR4 printed-circuit board.

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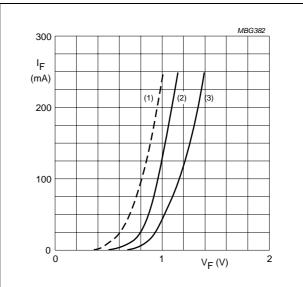
PMBD6050

GRAPHICAL DATA



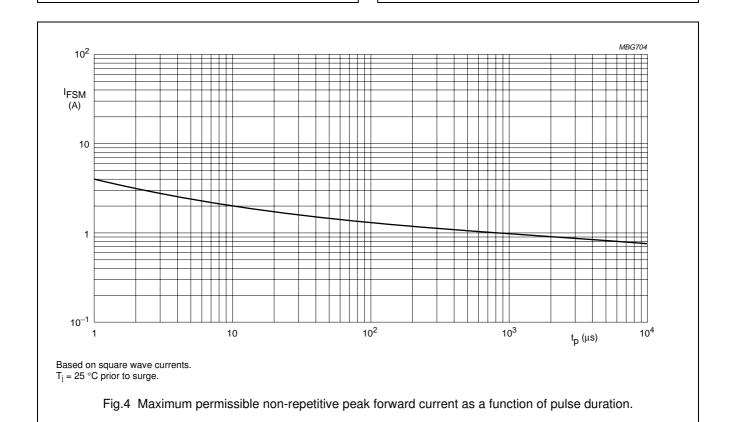
Device mounted on an FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



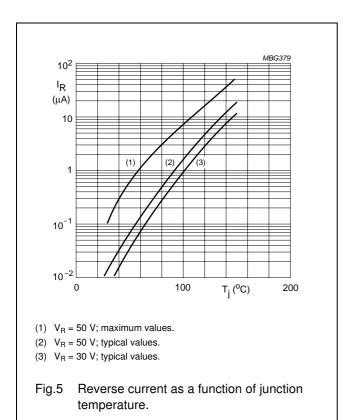
- (1) T_i = 150 °C; typical values.
- (2) $T_i = 25 \,^{\circ}\text{C}$; typical values.
- (3) $T_j = 25$ °C; maximum values.

Fig.3 Forward current as a function of forward voltage.



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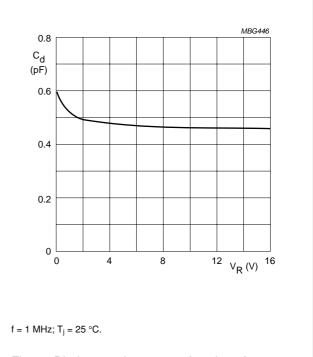
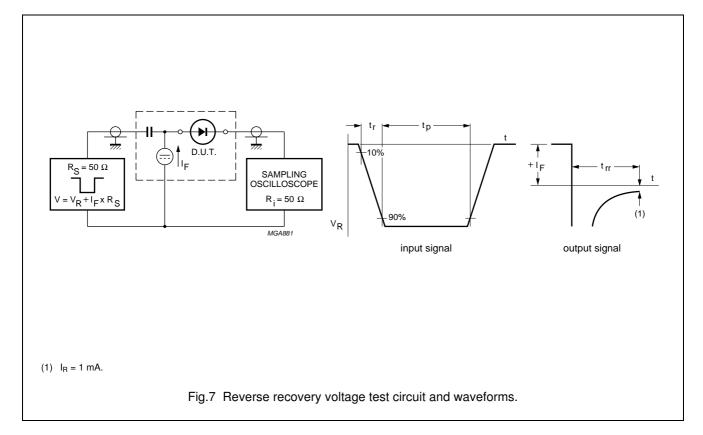
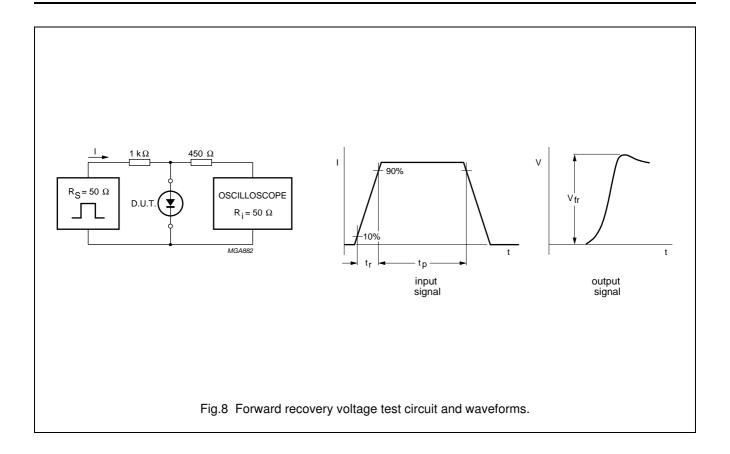


Fig.6 Diode capacitance as a function of reverse voltage; typical values.



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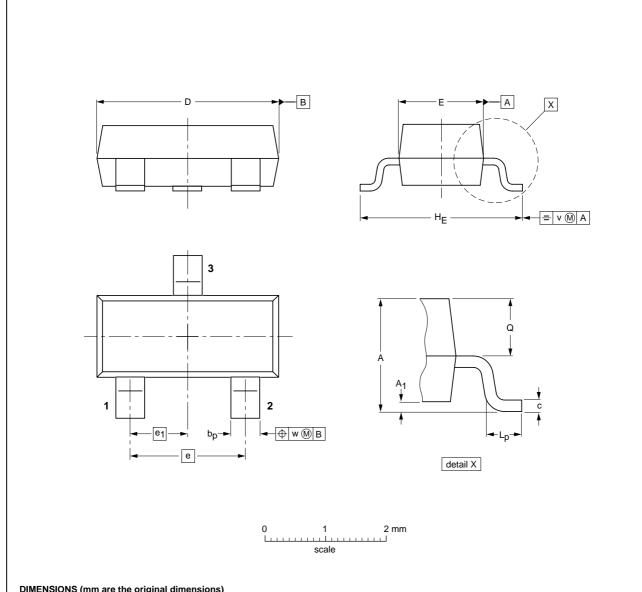
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PACKAGE OUTLINE



SOT23



DIMENSIONS (mm are the original dimensions)

| UNIT | Α | A ₁ max. | bp | С | D | E | е | e ₁ | HE | Lp | Q | v | w |
|------|------------|------------------------|--------------|--------------|------------|------------|-----|----------------|------------|--------------|--------------|-----|-----|
| mm | 1.1 0.9 | 0.1 | 0.48 0.38 | 0.15 0.09 | 3.0 2.8 | 1.4 1.2 | 1.9 | 0.95 | 2.5 2.1 | 0.45 0.15 | 0.55 0.45 | 0.2 | 0.1 |

| OUTLINE | | REFER | EUROPEAN | ISSUE DATE | | |
|---------|-----|----------|----------|------------|------------|----------------------------------|
| VERSION | IEC | JEDEC | JEITA | | PROJECTION | ISSUE DATE |
| SOT23 | | TO-236AB | | | | -04-11-04 06-03-16 |

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High-speed diode

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DATA SHEET STATUS

| DOCUMENT STATUS(1) | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|------------------------|----------------------------------|---|
| Objective data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
| Product data sheet | Production | This document contains the product specification. |

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Customer notification

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Contact information

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